

# 256-Kbit (32 K × 8) Static RAM

### **Features**

■ Temperature Ranges

□ Industrial: -40 °C to 85 °C
□ Commercial: 0 °C to 70 °C
□ Automotive-A: -40 °C to 85 °C

■ Single 3.3 V power supply

■ Ideal for low-voltage cache memory applications

■ High speed: 12 ns■ Low active power□ 180 mW (max)

■ Low-power alpha immune 6T cell

Available in pb-free and non pb-free plastic SOJ and TSOP-I packages

### **Functional Description**

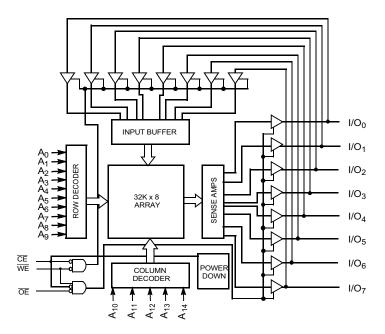
The CY7C1399BN is a high-performance 3.3 V CMOS Static RAM organized as 32,768 words by 8 bits. Easy memory expansion is provided by an active LOW Chip Enable (CE) and active LOW Output Enable (OE) and tristate drivers. The device has an automatic power-down feature, reducing the power consumption by more than 95% when deselected.

An active LOW Write Enable signal ( $\overline{\text{WE}}$ ) controls the writing/reading operation of the memory. When  $\overline{\text{CE}}$  and  $\overline{\text{WE}}$  inputs are both LOW, data on the eight data input/output pins (I/O<sub>0</sub> through I/O<sub>7</sub>) is written into the memory location addressed by the address present on the address pins (A<sub>0</sub> through A<sub>14</sub>). Reading the device is accomplished by selecting the device and enabling the outputs,  $\overline{\text{CE}}$  and  $\overline{\text{OE}}$  active LOW, while  $\overline{\text{WE}}$  remains inactive or HIGH. Under these conditions, the contents of the location addressed by the information on address pins is present on the eight data input/output pins.

The input/output pins remain in a high-impedance state unless the chip is selected, outputs are enabled, and Write Enable (WE) is HIGH. The CY7C1399BN is available in 28-pin standard 300-mil-wide SOJ and TSOP Type I packages.

For a complete list of related documentation, click here.

## **Logic Block Diagram**





## Contents

3
3
4
4
4
5
5
5
5
6
7
10
11
11

Раскаде Diagrams	12
Acronyms	14
Document Conventions	14
Units of Measure	14
Document History Page	15
Sales, Solutions, and Legal Information	16
Worldwide Sales and Design Support	16
Products	16
PSoC® Solutions	16
Cypress Developer Community	16
Technical Support	16



# **Pin Configurations**

Figure 1. 28-pin TSOP pinout (Top View)

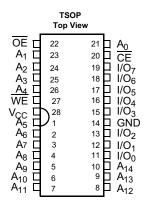


Figure 2. 28-pin SOJ pinout (Top View)



### **Selection Guide**

Description	Condition	-12	-15
Maximum access time (ns)		12	15
Maximum operating current (mA)		55	50
Maximum CMOS standby current (μA)	Commercial	500	_
	Commercial (L)	50	_
	Industrial	500	500
	Automotive-A	1	500



# **Maximum Ratings**

Output current into outputs (LOW)	)20 mA
Static discharge voltage (per MIL-STD-883, Method 3015)	>2001 V
Latch-up current	>200 mA

# **Operating Range**

Range	Ambient Temperature	V <sub>CC</sub>
Commercial	0 °C to +70 °C	$3.3~\textrm{V} \pm 300~\textrm{mV}$
Industrial	–40 °C to +85 °C	
Automotive-A	–40 °C to +85 °C	

### **Electrical Characteristics**

Over the Operating Range

Parameter [1]	Description	Test Conditions			-12		-15	11!4
Parameter 113	Description				Max	Min	Max	Unit
V <sub>OH</sub>	Output HIGH voltage	Min $V_{CC}$ , $I_{OH} = -2$ .	0 mA	2.4	_	2.4	_	V
V <sub>OL</sub>	Output LOW voltage	Min $V_{CC}$ , $I_{OL} = 4.0 \text{ m}$	nΑ	_	0.4	_	0.4	V
V <sub>IH</sub>	Input HIGH voltage			2.2	V <sub>CC</sub> + 0.3	2.2	V <sub>CC</sub> + 0.3	V
V <sub>IL</sub> <sup>[1]</sup>	Input LOW voltage			-0.3	0.8	-0.3	0.8	V
I <sub>IX</sub>	Input leakage current			-1	+1	-1	+1	μΑ
I <sub>OZ</sub>	Output leakage current	$GND \le V_{IN} \le V_{CC}, C$	utput disabled	<b>–</b> 5	+5	<b>-</b> 5	+5	μΑ
I <sub>CC</sub>	V <sub>CC</sub> operating supply current	$Max V_{CC}, I_{OUT} = 0 m$ $f = f_{MAX} = 1/t_{RC}$	Max V <sub>CC</sub> , I <sub>OUT</sub> = 0 mA,		55	_	50	mA
I <sub>SB1</sub>	Automatic CE power-down	$Max \ V_{CC}, \overline{CE} \ge V_{IH},$	Commercial	_	5	_	-	mA
	current – TTL inputs	$V_{IN} \ge V_{IH}$ , or $V_{IN} \le V_{IL}$ ,	Commercial (L)	_	4	_	_	mA
		$f = f_{MAX}$	Industrial	_	5	_	5	mA
			Automotive-A	_	-	_	5	mA
I <sub>SB2</sub>	Automatic CE Power-down	Max V <sub>CC</sub> ,	Commercial	_	500	_	_	μА
	current – CMOS inputs [2]	$\overline{\text{CE}} \ge \text{V}_{\text{CC}} - 0.3 \text{ V},$	Commercial (L)	_	50	_	_	μА
			Industrial	_	500	_	500	μΑ
		$\label{eq:VIN} \begin{aligned} V_{IN} &\geq V_{CC} - 0.3 \text{ V, or} \\ V_{IN} &\leq 0.3 \text{ V,} \end{aligned}$	Automotive-A	_	_	_	500	μА
		$WE \ge V_{CC} - 0.3 \text{ V or}$ $WE \le 0.3 \text{ V,}$ $f = f_{MAX}$						

### Notes

- 1. Minimum voltage is equal to  $-2.0\ V$  for pulse durations of less than 20 ns.
- Device draws low standby current regardless of switching on the addresses.

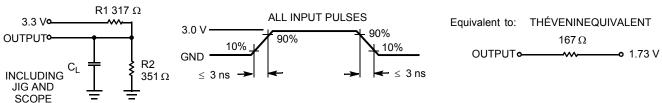


# Capacitance

Parameter [3]	Description	Test Conditions	Max	Unit
C <sub>IN</sub> : Addresses	Input capacitance	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz}, V_{CC} = 3.3 \text{V}$	5	pF
C <sub>IN</sub> : Controls			6	pF
C <sub>OUT</sub>	Output capacitance		6	pF

### **AC Test Loads and Waveforms**

Figure 3. AC Test Loads and Waveforms [4]



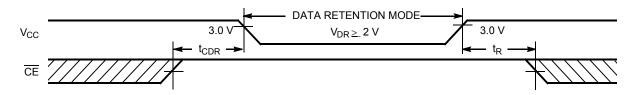
### **Data Retention Characteristics**

(Over the Operating Range - L version only)

Parameter	Description	Conditions	Min	Max	Unit
$V_{DR}$	V <sub>CC</sub> for data retention		2.0	_	V
I <sub>CCDR</sub>	Data retention current	$V_{CC} = V_{DR} = 2.0 \text{ V},$	0	20	μΑ
t <sub>CDR</sub>	Chip deselect to data retention time	$\overrightarrow{CE} \ge V_{CC} - 0.3 \text{ V},$ $V_{IN} \ge V_{CC} - 0.3 \text{ V or } V_{IN} \le 0.3 \text{ V}$	0	-	ns
t <sub>R</sub>	Operation recovery time		t <sub>RC</sub>	_	ns

### **Data Retention Waveform**

Figure 4. Data Retention Waveform



### Notes

- Tested initially and after any design or process changes that may affect these parameters.
- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I<sub>OL</sub>/I<sub>OH</sub> and capacitance C<sub>L</sub> = 30 pF.



# **Switching Characteristics**

Over the Operating Range

5	Description		12		15	11!4
Parameter [5]	Description	Min	Max	Min	Max	Unit
Read Cycle			•	•	•	
t <sub>RC</sub>	Read cycle time	12	-	15	_	ns
t <sub>AA</sub>	Address to data valid	_	12	-	15	ns
t <sub>OHA</sub>	Data hold from address change	3	_	3	_	ns
t <sub>ACE</sub>	CE LOW to data valid	_	12	_	15	ns
t <sub>DOE</sub>	OE LOW to data valid	_	5	_	6	ns
t <sub>LZOE</sub>	OE LOW to low Z [6]	0	_	0	_	ns
t <sub>HZOE</sub>	OE HIGH to high Z [6, 7]	_	5	_	6	ns
t <sub>LZCE</sub>	CE LOW to low Z [6]	3	_	3	_	ns
t <sub>HZCE</sub>	CE HIGH to high Z [6, 7]	_	6	_	7	ns
t <sub>PU</sub>	CE LOW to power-up	0	_	0	_	ns
t <sub>PD</sub>	CE HIGH to power-down	_	12	_	15	ns
Write Cycle [8,	9]		•	•	•	
t <sub>WC</sub>	Write cycle time	12	_	15	_	ns
t <sub>SCE</sub>	CE LOW to write end	8	_	10	_	ns
t <sub>AW</sub>	Address setup to write end	8	_	10	_	ns
t <sub>HA</sub>	Address hold from write end	0	_	0	_	ns
t <sub>SA</sub>	Address setup to write start	0	_	0	_	ns
t <sub>PWE</sub>	WE pulse width	8	_	10	_	ns
t <sub>SD</sub>	Data setup to write end	7	_	8	_	ns
t <sub>HD</sub>	Data hold from write end	0	_	0	_	ns
t <sub>HZWE</sub>	WE low to high Z <sup>[8]</sup>	_	7	_	7	ns
t <sub>LZWE</sub>	WE high to low Z <sup>[6]</sup>	3	_	3	_	ns

### Notes

<sup>5.</sup> Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I<sub>OL</sub>/I<sub>OH</sub>

 <sup>1.</sup> lest conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I<sub>OL</sub>/I<sub>OH</sub> and capacitance C<sub>L</sub> = 30 pF.
 At any given temperature and voltage condition, t<sub>HZCE</sub> is less than t<sub>LZCE</sub>, t<sub>HZOE</sub> is less than t<sub>LZOE</sub>, and t<sub>HZWE</sub> is less than t<sub>LZWE</sub> for any given device.
 t<sub>HZOE</sub>, t<sub>HZCE</sub>, t<sub>HZWE</sub> are specified with C<sub>L</sub> = 5 pF as in AC Test Loads. Transition is measured ±500 mV from steady state voltage.
 The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
 The minimum write cycle time for Write Cycle No. 3 (WE Controlled, OE LOW) is the sum of t<sub>HZWE</sub> and t<sub>SD</sub>.



# **Switching Waveforms**

Figure 5. Read Cycle No. 1 [10, 11]

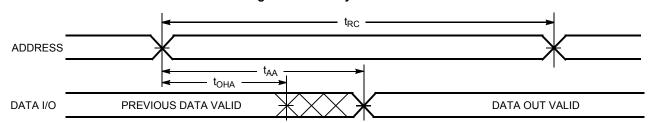
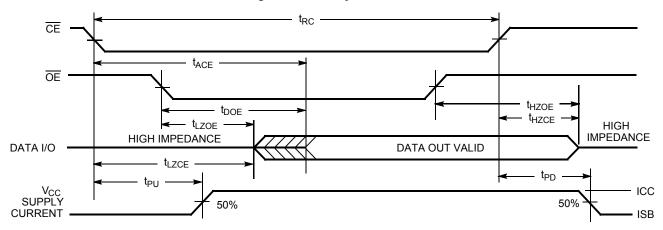


Figure 6. Read Cycle No. 2 [11, 12]



<sup>10. &</sup>lt;u>Device</u> is continuously selected. <del>OE</del>, <del>CE</del> = V<sub>IL</sub>.

11. <u>WE</u> is HIGH for read cycle.

12. Address valid prior to or coincident with <del>CE</del> transition LOW.



# Switching Waveforms (continued)

Figure 7. Write Cycle No. 1 (WE Controlled) [13, 14, 15]

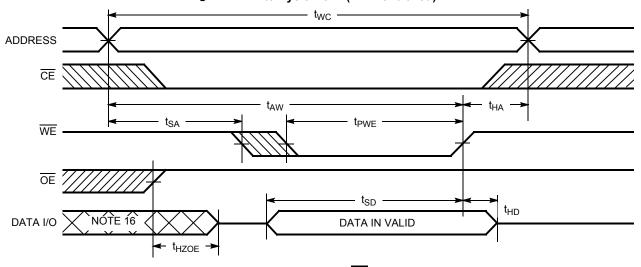
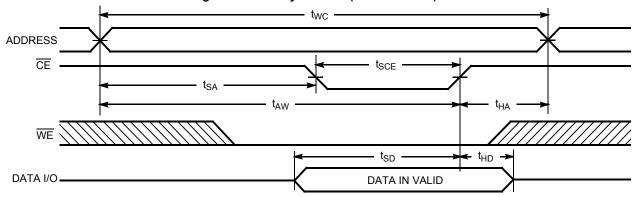


Figure 8. Write Cycle No. 2 ( $\overline{\text{CE}}$  Controlled) [13, 14, 15]



<sup>13.</sup> The internal write time of the memory is defined by the overlap of  $\overline{CE}$  LOW and  $\overline{WE}$  LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.

14. Data I/O is high impedance if  $\overline{OE} = V_{|H:}$ 15. If  $\overline{CE}$  goes HIGH simultaneously with WE HIGH, the output remains in a high-impedance state.

16. During this period, the I/Os are in the output state and input signals should not be applied.



# **Switching Waveforms** (continued)

Figure 9. Write Cycle No. 3 (WE Controlled, OE LOW) [17, 18] - t<sub>WC</sub> **ADDRESS**  $t_{\text{HA}} \\$ WE  $t_{\text{SD}}$  $t_{\text{HD}}$ DATA I/O NOTE 19 DATA IN VALID – t<sub>LZWE</sub> –

<sup>17.</sup> If CE goes HIGH simultaneously with WE HIGH, the output remains in a high-impedance state.

18. The minimum write cycle pulse width should be equal to the sum of t<sub>HZWE</sub> and t<sub>SD</sub>.

19. During this period, the I/Os are in the output state and input signals should not be applied.



# **Truth Table**

CE	WE	OE	Input/Output	Mode	Power
Н	Х	Х	High Z	Deselect/Power-down	Standby (I <sub>SB</sub> )
L	Н	L	Data Out	Read	Active (I <sub>CC</sub> )
L	L	Х	Data In	Write	Active (I <sub>CC</sub> )
L	Н	Н	High Z	Deselect, Output disabled	Active (I <sub>CC</sub> )



## **Ordering Information**

Cypress offers other versions of this type of product in many different configurations and features. The following table contains only the list of parts that are currently available.

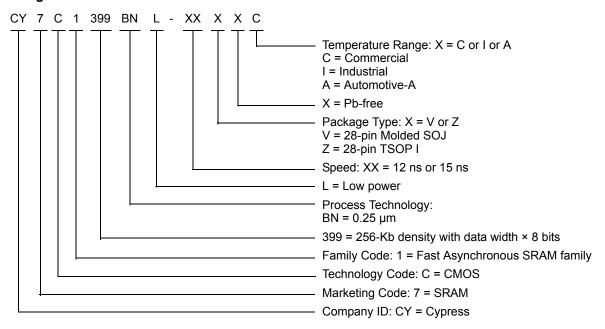
For a complete listing of all options, visit the Cypress website at www.cypress.com and refer to the product summary page at http://www.cypress.com/products or contact your local sales representative.

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Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
12	CY7C1399BN-12ZXC	51-85071	28-pin TSOP I (Pb-free)	Commercial
	CY7C1399BNL-12ZXC		28-pin TSOP I (Pb-free)	
	CY7C1399BN-12VXI	51-85031	28-pin molded SOJ (Pb-free)	Industrial

Contact your local sales representative regarding availability of these parts.

### **Ordering Code Definitions**





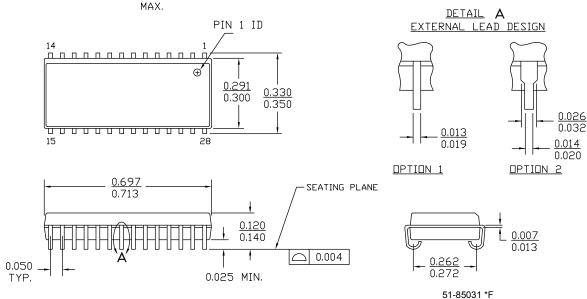
## **Package Diagrams**

### Figure 10. 28-pin SOJ (300 Mils) V28.3 (Molded SOJ V21) Package Outline, 51-85031

28 Lead (300 Mil) Molded SOJ V21

### NDTE :

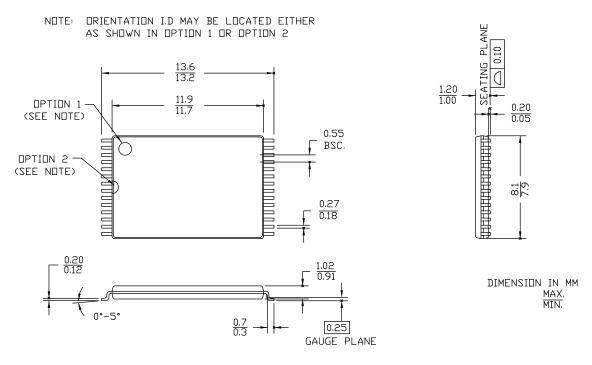
- 1. JEDEC STD REF MO088
- 2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.006 in (0.152 mm) PER SIDE
- 3. DIMENSIONS IN INCHES MIN.





# **Package Diagrams (continued)**

Figure 11. 28-pin TSOP I (8 × 13.4 × 1.2 mm) Z28 (Standard) Package Outline, 51-85071



51-85071 \*J



# **Acronyms**

Acronym	Description
CE	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
OE	Output Enable
SRAM	Static Random Access Memory
TSOP	Thin Small Outline Package
WE	Write Enable

# **Document Conventions**

### **Units of Measure**

Symbol	Unit of Measure			
°C	degree Celsius			
MHz	megahertz			
μΑ	microampere			
mA	milliampere			
mV	millivolt			
mW	milliwatt			
ns	nanosecond			
pF	picofarad			
V	volt			
W	watt			



# **Document History Page**

Document Title: CY7C1399BN, 256-Kbit (32 K × 8) Static RAM Document Number: 001-06490					
Revision	ECN	Orig. of Change	Submission Date	Description of Change	
**	423877	NXR	See ECN	New data sheet.	
*A	498575	NXR	See ECN	Added Automotive-A range related information in all instances across the document. Updated Electrical Characteristics: Removed I <sub>OS</sub> parameter and its details. Updated Ordering Information.	
*B	2896382	AJU	03/19/2010	Updated Ordering Information: Removed obsolete part numbers. Updated Package Diagrams.	
*C	3053362	PRAS	10/08/2010	Updated Ordering Information: Removed pruned part numbers CY7C1399BNL-15VXC and CY7C1399BNL-15VXCT. Added Ordering Code Definitions.	
*D	3383869	TAVA	09/26/2011	Rearranged sections for better clarity. Updated Features: Added Commercial Temperature Range related information. Updated Functional Description: Removed Note "For guidelines on SRAM system design, please refer to the 'System Design Guidelines' Cypress application note, available on the interneat www.cypress.com website." and its reference. Updated Switching Waveforms: Modified the notes in figures under Read cycle and Write cycle sections. Updated Package Diagrams. Added Acronyms and Units of Measure. Updated to new template.	
*E	4121360	VINI	09/12/2013	Updated to new template. Completing Sunset Review.	
*F	4540416	VINI	10/16/2014	Updated Switching Waveforms: Updated Note 18. Updated Package Diagrams: spec 51-85071 – Changed revision from *I to *J. Completing Sunset Review.	
*G	4578447	VINI	01/16/2015	Updated Functional Description: Added "For a complete list of related documentation, click here." at the end. Updated Ordering Information: Removed the prune part numbers CY7C1399BN-12VXC and CY7C1399BN-15VXA. Updated Package Diagrams: spec 51-85031 – Changed revision from *E to *F. Updated to new template.	
*H	4985705	NILE	10/24/2015	No technical updates. Completing Sunset Review.	



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